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5 **Energy Level Alignment at Metal/Solution-Processed Organic Semiconductor Interfaces**

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44 The optimization of the performance of organic-based devices such as organic photovoltaic  
45 cells (OPV), organic light emitting diodes (OLED) and organic field effect transistors (OFET)  
46 has been the subject of intensive research over the past twenty years.<sup>[1-4]</sup> Due to such research  
47 efforts, the key role of the energy barriers built up between the metal Fermi level and the  
48 molecular levels devoted to charge transport for the device performance has been  
49 elucidated.<sup>[5-7]</sup> Typically, techniques such as electron photoemission spectroscopy, Kelvin  
50 probe measurements and in-device hot electron spectroscopy have been applied to the study  
51 of interfacial energy barriers.<sup>[8-13]</sup> The first two methods are limited to extract the energy  
52 level alignment by monitoring the change in the work function for thin molecular layers  
53 evaporated on the surface of a metal. They require complex equipment and are far from being  
54 implemented into device architecture. The third method, hot electron spectroscopy, has  
55 however opened the possibility to determine energy barriers between a metal and an organic  
56 semiconductor without using any material parameters and in-device operative conditions.<sup>[12,</sup>  
57 <sup>13]</sup> This advantage occurs by the ability of monitoring the current flow in a three-terminal  
58 device, which is directly related with metal/semiconductor charge injection energy barriers.  
59 However, challenges and questions still remain regarding to this last technique. Consequently,  
60 in this article we would like to tackle a two-fold problem.

61  
62 On the one side, hot electron devices have not yet been demonstrated in *ex-situ* fabrication  
63 conditions with polymers. These materials are closer to industrial applications for plastic  
64 electronics (OPV, OLED, OFET, etc.) than many small molecules considering that they can  
65 be processed over large areas at low cost. Establishing this method as a quick, direct  
66 procedure for the measurement of the metal/polymeric semiconductor energy barrier could be  
67 of great interest. So far there are no suitable methods that enable the measurement of  
68 metal/lowest unoccupied molecular orbital (LUMO) interfaces when dealing with polymers.

69 The most powerful one is probably inverse photoemission electron spectroscopy (IPES).<sup>[14]</sup>  
70 However, its low resolution and the damage it creates to the organic film by exposing the  
71 sample to energetic electrons limits its use only to well-established small molecules such as  
72 C<sub>60</sub> or 3,4,9,10-Perylentetracarbonsäuredianhydrid (PTCDA).<sup>[14]</sup> On the other side, from a  
73 more basic point of view, there are still concerns regarding the effects of impurity layers  
74 consequence of *ex-situ* fabrication techniques on the energy barrier alignment between the  
75 metal and the organic semiconductor and thus, on the charge injection into the semiconductor.  
76 A device approach is hence required to solve this question, which ramifies the field of organic  
77 electronics from fundamental understanding to industrial applications.

78  
79 In this communication we measure the interfacial energy barrier between metals and the  
80 solution processed electron-transporting polymer, poly{[N, N'-bis(2-octyldodecyl)-  
81 naphthalene-1,4,5,8-bis(dicarboximide)-2,6-dyl]-*alt*-5,5'-(2,2'-dithiophene)}[P(NDI2OD-T2),  
82 PolyeraActivInk<sup>TM</sup> N2200] by using in-device hot-electron spectroscopy.<sup>[15]</sup> We chose this  
83 particular polymer due to its high electron mobility and stability under ambient conditions,  
84 which have led to promising technological applications.<sup>[15-17]</sup> The devices were fabricated by  
85 spin coating the polymer solution in air, i.e. far from ideal ultra clean conditions that are  
86 obtained with *in-situ* evaporation, but also potentially cheaper and scalable.

87  
88 Our novel results regarding the interfacial energy barrier and the role of the *ex-situ* created  
89 contamination layer between the metal and the polymer are supported by standard ultraviolet  
90 photoemission spectroscopy (UPS) measurements.<sup>[9]</sup> Contrary to IPES, UPS is an indirect  
91 method as it can only probe occupied states and diverse approximations must be done for  
92 reaching a metal/LUMO energy value. However, the damage produced in the organic film and  
93 the low resolution obtained with the former method have made UPS a more suitable technique  
94 for the extraction of metal/LUMO energy barriers. The data is complemented with the

95 development of a theoretical model, which reconciles the electron photoemission results with  
96 those coming from electrical transport. This work gives a further understanding of the energy  
97 barriers built up between metals and polymeric semiconductors considering realistic  
98 interfaces while demonstrating the power and potential of the in-device hot electron  
99 spectroscopy for the determination of these energy barriers.

100

101 The first method we have used for the extraction of metal/solution processed organic  
102 semiconductor interface energy barriers is in-device hot electron spectroscopy. Although this  
103 technique was first applied for the determination of the energy level alignment at  
104 metal/inorganic semiconductor and metal/small molecule semiconductor interfaces, in this  
105 work, for the first time, we use in-device hot-electron spectroscopy for the determination of  
106 energy barriers between a metal and a polymeric semiconductor.<sup>[10, 18, 12, 13]</sup> The working  
107 principle is shown in **Figure 1**. In more detail, our three-terminal device is composed of an  
108 emitter, a base and a collector. The emitter is a 13 nm-thick aluminum contact, which later is  
109 plasma-oxidized *in-situ* to create an AlO<sub>x</sub> tunnel barrier. 10 nm of gold are evaporated as base  
110 contact. Gold was chosen for being a commonly used material for device contacts. Its air  
111 stability and noble properties make it a suitable metal for, among others, pre-patterned devices.  
112 This emitter-base sample is spin coated with a solution of N2200 (see Experimental Section)  
113 in ambient conditions inside the clean room. The polymer is the collector of the system. A 13-  
114 nm-thick Al top electrode is used to receive the collector current from the semiconductor. In  
115 these devices, the energy level alignment between the Fermi level of emitter and base is  
116 externally controlled with a bias between emitter and base  $V_{EB}$  (see Figure 1), while the  
117 energy alignment at the base/collector interface is naturally given by the metal/polymer  
118 energy barrier  $\Delta$ .

119

120 When a negative bias  $V_{EB}$  is applied a current  $I_E$  is injected from the emitter into the device by  
121 tunneling through the AlOx barrier. These electrons are “hot” in the base as their energy is  
122 above the Fermi energy of the metal, and a fraction of them cross the base ballistically  
123 without energy attenuation.<sup>[19]</sup> If the applied external voltage  $V_{EB}$  is lower than the barrier  $\Delta$ ,  
124 the ballistic electron current is reflected at the Au/N2200 interface and no collector current is  
125 measured ( $I_{C-hot}=0$ ) since it will flow instead into the base terminal ( $I_B$ ). On the contrary, if  
126  $V_{EB}$  is higher than the barrier  $\Delta$  (Figure 1), some of the hot electrons enter in the LUMO level  
127 of N2200, diffuse towards the top Al electrode and a current is measured in the collector ( $I_{C-}$   
128  $hot \neq 0$ ). We point out that since N2200 is an n-type semiconductor, we measure the energy  
129 barrier between the Fermi level of the gold base and the LUMO of the polymer, which is the  
130 one devoted to the charge transport. Since the base electrode is kept at ground potential  
131 (Figure 1),  $V_{EB}$  must be negative to inject hot electrons from the emitter into the base and then  
132 to the polymer layer. Importantly, the current  $I_{C-hot}$  is measured without any external applied  
133 bias between the base and collector and thus,  $I_{C-hot}$  can be considered as a purely diffusive  
134 current. This is possible due to both the momentum of the injected electrons perpendicular to  
135 the Au/N2200 interface and to the built-in potential created by sandwiching the polymer with  
136 two metallic contacts with different work functions.<sup>[20, 21]</sup>

137  
138 Figure 2 shows the typical characterization of the device for temperatures from 290 K to 110  
139 K. The  $I_E$ - $V_{EB}$  characteristics of the tunnel junction (Al/AlOx/Au stack) are shown in Figure  
140 2a. The resistance slightly increases when lowering the temperature as expected for non-leaky  
141 tunnel junction.<sup>[22]</sup> Complementarily, from standard diode measurements to Au/N2200/Al,  
142 by applying an external bias between the base and collector,  $V_{BC}$ , we observe a rectifying  
143 behavior where the diode current,  $I_{diode}$ , is higher when electrons are injected by the top Al  
144 layer ( $V_{BC} < 0$ ) than when they are injected from the base gold ( $V_{BC} > 0$ ) (see Figure S1 and  
145 Supplementary Note 1). This behavior suggests the formation of a high-energy barrier at the

146 Au/N2200 interface. Figure 2b shows the  $I_{C-hot}-V_{EB}$  characteristics of the device at the same  
147 set of temperatures. We observe that  $I_{C-hot}$  is 4 orders of magnitude lower than  $I_E$ . This is a  
148 characteristic behavior of hot electrons in semiconductors.[12] Figure 2c shows  $I_{C-hot}$  versus  
149  $V_{EB}$  at 290 K together with the linear fit of the growth of the current to the  $I_{C-hot} = 0$  line.[21]  
150 Using this straightforward method the energy barrier  $\Delta$  between Au and N2200 is estimated to  
151 be  $1.2 \pm 0.1$  V (dotted blue arrow). We fabricated four chips containing several devices each  
152 in different deposition rounds. The average barrier value measured was  $1.2 \pm 0.1$  V. The  
153 device-to-device variation in each chip is lower than the measurement precision, while the  
154 maximum variation from chip to chip is 0.1V. More complex fittings that consider the  
155 tunneling probability and the density of states of the semiconductor can be also employed for  
156 the reproduction of the curves, but the ultimate results are in any case extremely similar.[12]  
157 The dotted green arrow points out the onset of the non zero  $I_{C-hot}$  at  $0.9 \pm 0.1$  V, which  
158 corresponds to the energy barrier for charge injection into the polymer interface states.[12]  
159  
160 Hot electron spectroscopy provides information about the metal/semiconductor energy  
161 barriers in device operative conditions as well as how this interfacial energy determines the  
162 charge injection into the semiconductor. Complementary to this, in order to verify the  
163 metal/semiconductor energy barrier, well established methods such as UPS can be used.<sup>[9, 23]</sup>  
164 This technique probes the ionization energies of the occupied electronic density of states  
165 without the lattice relaxation energy that can occur upon photoemission of an electron (see  
166 Experimental Section). **Figure 3a** shows the HeI survey scan of a N2200 film on gold. The  
167 frontier edge of the occupied electronic structure is typically taken as the vertical ionization  
168 potential (IP) referenced to the Fermi energy (0 eV) in the figure. To get an IP value  
169 referenced to the vacuum level, the work function of the sample is determined from the so-  
170 called secondary electron cut-off, **Figure 3b**. The UPS measurements carried out gave an IP  
171 of  $5.7 \pm 0.1$  eV with work functions of  $4.7 \pm 0.1$  eV. A negative pinning energy of  $3.9 \pm 0.1$  eV

172 (corresponding to the energy of a singly occupied LUMO at the polymer-gold interface  
173 screened by the image charge of the gold surface, see Supplementary Note 2) was also  
174 obtained from UPS measurements, in good agreement with Kelvin probe derived results in  
175 literature.<sup>[24]</sup> The small variation in work function ( $\pm 0.1$  eV) between films is partly the  
176 experimental error but also due to variation in the starting gold surface as well as film  
177 formation at the Au/N2200 interface, and is in the range of previous studies of polymer-gold  
178 interfaces.<sup>[25]</sup> The electron injection barrier at the Au/N2200 interface can then be estimated  
179 from the UPS values as  $4.7$  eV  $-$   $3.9$  eV =  $0.8 \pm 0.1$  eV. However, we must consider that this  
180 barrier represent injection of an electron into the edge of the N2200 n-polaron (relaxed singly-  
181 occupied LUMO) distribution at the gold interface, where the image charge effect shifts the  
182 energy deeper into the gap compared to the bulk n-polaron distribution (see **Figure 3c**), a  
183 well-known effect from both device physics and interface energy level alignment.<sup>[26-28]</sup> The  
184 size of the shift going from interface to bulk depends on a variety of factors including the  
185 organic film morphology and its dielectric constant, with values in literature ranging between  
186  $0.3$  eV up to  $0.7$  eV.<sup>[27-29]</sup> Hence, the electrons injected into the edge states are bound at the  
187 interface and will not make it to the collecting contact as no driving voltage is applied (see  
188 simulations below). In fact, only electrons injected near the center ( $\sim 0.5 \sigma$ , being  $\sigma$  the width  
189 of the Gaussian energy disorder) of the bulk n-polaron distribution are expected to contribute  
190 to the current under these conditions (see Figure 3c).<sup>[30, 31]</sup> Taking the lower value of  $0.3$  eV  
191 for the image charge induced shift between interface and bulk we get a total barrier for the  
192 conditions of ballistic injection current in the device as  $0.8$  eV +  $0.3$  eV =  $1.1$  eV. Both the  
193 interface energy barrier and bulk energy barrier values are in good agreement with the direct  
194 experimental observation performed by in-device hot electron spectroscopy, albeit if several  
195 approximation have been needed for the extraction of the bulk energy barrier.

196

197 UPS measurements show a change in the work function of the gold contact coming from its  
198 air exposure, which is a well-known experimental result reported extensively in literature  
199 (Figure 3b and Ref. 16). However, it is not clear if such contamination layer might modulate  
200 the energy barrier values when these are measured by in-device hot electron spectroscopy. In  
201 order to disentangle this question, we fabricate a hot electron device in which the gold  
202 interface is cleaned with oxygen plasma for 5 minutes just before the spin coating of the  
203 polymer. **Figure 3d** shows the measured hot-electron current normalized to  $I_{C-hot}/I_{C-hot(max)}$  as  
204 a function of the applied bias  $V_{EB}$  at 290 K corresponding to both samples, one with clean  
205 gold (black line) and a standard device with untreated gold (red line).  $I_{C-hot(max)}$  corresponds to  
206 the maximum value of the measured hot-electron current. No difference in the energy barrier  
207 value is observed when we compare both samples, indicating that a contamination layer  
208 coming from air exposure of gold does not affect substantially the carrier injection in  
209 agreement with UPS literature on gold/polymer contacts.<sup>[32]</sup>

210

211 For a better understanding of our results we have developed a theoretical model for the hot-  
212 electron transistor. The model is kept simple but includes the different parts of the device as  
213 illustrated in **Figure 4a**. The central part is the polymer film, represented as hopping sites  
214 (balls), which is sandwiched between gold and aluminum electrodes. Hot-carriers can be  
215 injected with a rate  $\nu$  through the base into the polymer as illustrated by black arrows in  
216 Figure 4a. The charge transport in the polymer is modeled as hopping transport between  
217 localized states (sticks between balls), while electron transfer from Au (Al) into the polymer  
218 and back is possible via the Au (Al) Fermi level. We solve the Poisson equation and transport  
219 Master equation simultaneously (see Experimental Section for details) for a steady state.

220

221 In the simulations, we assume hot carrier operation conditions by setting  $V_{BC} = 0V$  ( $\Phi = 0$  eV  
222 is the metal Fermi level). When no hot electrons are provided at the base ( $\nu = 0$ ), we expect  
223 the electron affinity of the polymer interface states, which is increased by an image charge of  
224 0.3 eV, to be at 3.8 eV (i.e.  $\Phi = 0.9$  eV). This choice for the energy level of the lowest polymer  
225 states at 0.1 eV above the pinning onset of 3.9 eV is due to interfacial energetic disorder and  
226 finite temperature which leads to the onset of charging of the lowest polymer states (pinning)  
227 at such offset. When hot electrons are provided with a finite rate  $\nu$  and  $V_{EB} = -1.2$  V, the  
228 solution of the equations yields the potential distribution shown in **Figure 4b**. The resulting  
229 potential is dominated by the built-in potential and the image-charge potential close to the  
230 Au/N2200 interface. In addition, a small space-charge contribution close to the interface  
231 occurs at the chosen injection conditions.

232

233 **Figure 4c** summarizes the calculated  $I_{C-hot}$  for varying  $V_{EB}$ . At small hot-electron energy  
234 ( $|V_{EB}| \leq 1.1$  V) the electrons can hardly reach the transport levels of the bulk polymer although  
235 the lowest polymer states close to the interface may be populated, i.e. electrons cannot escape  
236 the barrier from the image-charge and  $I_{C-hot}$  is suppressed. This barrier can be overcome by  
237 further increasing  $|V_{EB}|$ , which provides more electrons with higher energies. Note that the  
238 hot-electrons arrive with energies continuously distributed between zero and  $|V_{EB}|$ . This leads  
239 to the current onset at  $V_{EB} = -1.2$  eV (from a linear fit) and further linear increase in  $I_{C-hot}$ .  
240 These results are in good agreement with the ones obtained by in-device hot electron  
241 spectroscopy.

242

243 In conclusion, we have shown that in-device hot electron spectroscopy is a reliable and  
244 straightforward method for the determination of metal/polymeric semiconductor energy  
245 barriers, making their use convenient for the engineering of commercial ex-situ fabricated

246 organic electronic devices. Our research also makes in-device hot electron spectroscopy a  
247 handy tool for the general research community working in organics, as its use is available for  
248 laboratories, which do not use ultra-high vacuum evaporation systems. Our results are  
249 confirmed by an established technique such as UPS. This shows to be a reliable, but non-  
250 direct, method for the determination of interfacial transport energy barriers, thus highlighting  
251 the importance of our direct method. Along the article we have also explored the role of the  
252 contamination layer coming from the air exposure of the devices in the fabrication process,  
253 we have seen that it does not play a significant role. Our experimental work has been  
254 complemented by a theoretical model developed for transport in hot electron devices. This  
255 model has given a further understanding on the role of the interfaces in hot electron devices as  
256 well as highlighting the existing differences between the two techniques employed. This work  
257 gives a new approach to the study of metal/polymeric semiconductor interfaces as well as  
258 providing a new design tool for organic electronics.

259  
260

## 261 **Experimental Section**

262 *Device fabrication:* All metallic parts of the devices described in this work were fabricated  
263 in ultra high vacuum (UHV) evaporator chamber (base pressure  $<10^{-9}$  mbar) with a shadow  
264 mask system. Metals (99.95%) (Lesker) were evaporated by e-beam at a rate of  $0.1 \text{ nm s}^{-1}$ .

265

266 The organic layer was ex-situ spin coated in clean room at ambient conditions. The solution  
267 was prepared with 5mg of N2200 ( $> 99.5\%$ ) (PolyeraActivInk<sup>TM</sup>) dissolved in 1 ml of  $\text{CHCl}_3$   
268 (99.9%)(extra dry, stabilized) (AcroSeal).  $90 \mu\text{l}$  of this solution were spin coated on the  
269 sample for 60s at 4000 rpm. In order to evaporate the residual solvent in the sample before the  
270 evaporation of the top metallic contact, this was kept in vacuum ( $10^{-6}$  mbar) for two hours.

271

272 *Electrical characterization:* Electrical characterization was performed under high vacuum  
273 (base pressure  $5 \times 10^{-5}$  mbar) in a variable-temperature probe-station (Lakeshore). A Keithley  
274 4200 semiconductor analyzer system was used to record  $I$ - $V$  curves.

275

276 *Photoelectron spectroscopy:* Measurements were carried out in a UHV surface analysis  
277 system equipped with a Scienta-200 hemispherical analyzer. The base pressure of the sample  
278 analysis chamber was  $2 \times 10^{-10}$  mbar. UPS was performed using a standard He-discharge  
279 lamp with HeI 21.22 eV as excitation source and an energy resolution of 50 meV. Radiation  
280 damage was tested for and found not to occur. The work functions were derived from the  
281 secondary electron cut-off, and XPS was measured using monochromatized Al Ka with  $h\nu =$   
282 1486.6 eV. All measurements were calibrated by referencing to the Fermi level and Au 4f<sub>7/2</sub>  
283 peak position of an Ar<sup>+</sup> ion sputter-clean gold foil.

284

285 *Modeling:* All device simulations are based on a master equation approach taking into account  
286 the electric field distribution through the solution of the 1D Poisson equation, the image  
287 charge potential, a random disorder potential of  $\sigma = 0.1$  eV at the interfaces and the built-in  
288 potential coming from the different work functions of the electrodes.<sup>[33]</sup> The tunneling rates of  
289 the hot electrons into the polymer layer decay exponentially away from the Au surface.  
290 Miller-Abraham hopping rates are used between sites within the polymer and for the hopping  
291 between the polymer and the Au and Al levels.<sup>[34]</sup> To calculate the hot-electron current, we  
292 note that the hot electrons from the base enter the polymer region with energy equal or below  
293  $-eV_{EB}$  and can contribute to the current  $I_{C-hot}$ . Therefore,  $I_{C-hot}$  is obtained from integrating  
294 these contributions up to  $-eV_{EB}$ .

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298 **Supporting Information**

299 Supporting Information is available from the Wiley Online Library or from the author.

300

301

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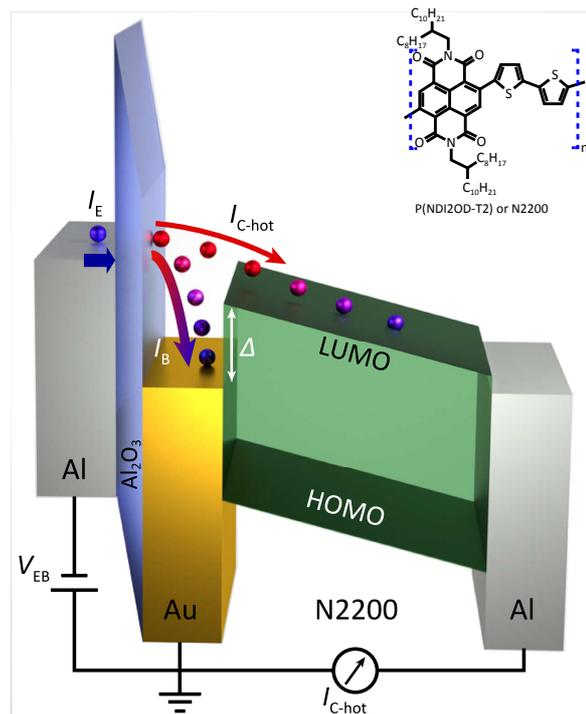
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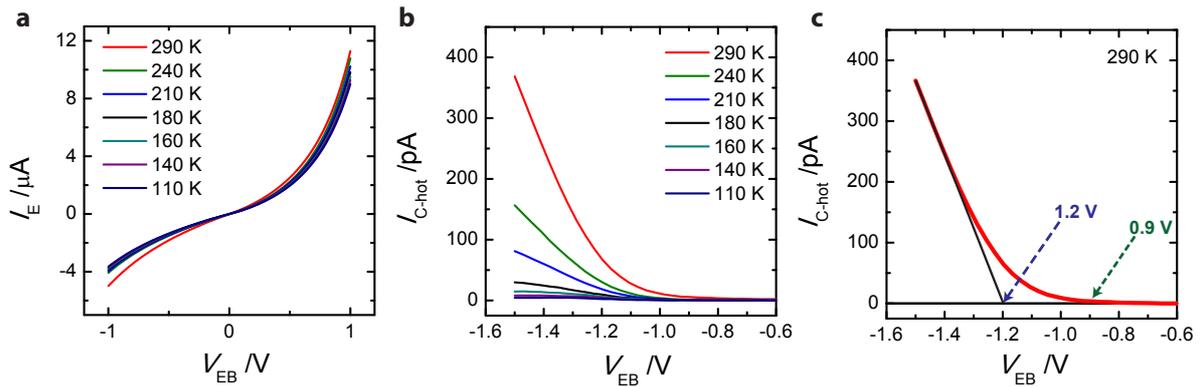
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417 **Figure 1.** Scheme of the working principle and the energy levels of the device in rigid band  
418 approximation. The tunneling current  $I_E$  flows from the emitter to the base when a negative  
419 bias  $V_{EB}$  is applied at the emitter/base terminals. A major part of this injected current is  
420 attenuated in the base and collected as  $I_B$  while the other part of  $I_E$  flows ballistically to the  
421 base/collector interface. When the bias  $V_{EB}$  is higher than  $\Delta$ , a fraction of the  $I_E$  flows into the  
422 N2200 and is measured as  $I_{C-hot}$ . This current is collected without any external bias applied  
423 between the base and the collector terminals. Inset: chemical structure of P(NDI2OD-T2) or  
424 N2200 polymer.

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 428 **Figure 2.** Electrical characterization of the device. a) Temperature dependence of the emitter  
 429 current  $I_E$  measured at two terminals in the Al/AlOx/Au tunnel junction as a function of  
 430 applied bias  $V_{EB}$ . b) Temperature dependence of the hot-electron current  $I_{C\text{-hot}}$  measured in the  
 431 Au/N2200/Al stack as a function of the applied bias  $V_{EB}$ . c)  $I_{C\text{-hot}}$  measured as a function of  
 432 the applied bias between the emitter and the base  $V_{EB}$  at 290 K and the linear fit to  $I_{C\text{-hot}} = 0$  to  
 433 obtain the barrier height  $\Delta$ .

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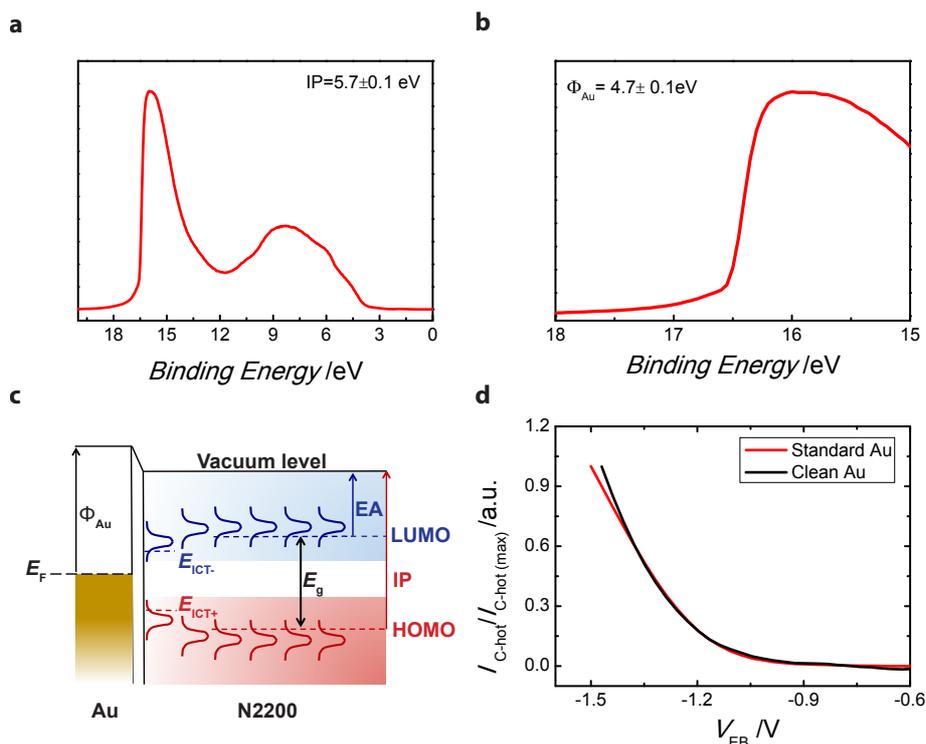
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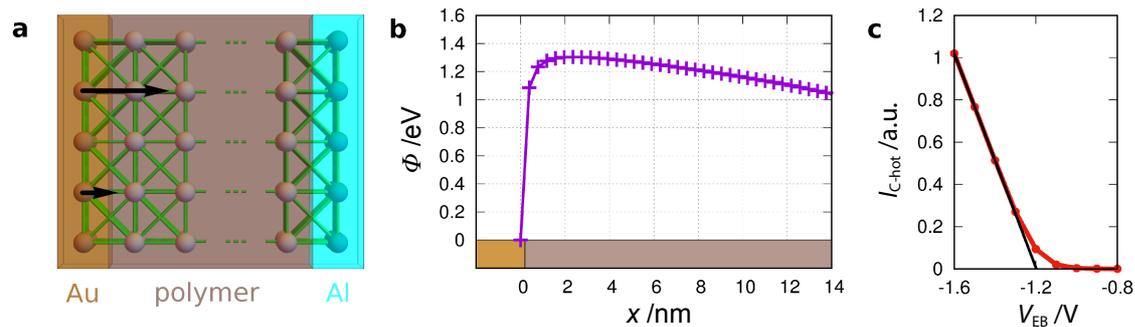
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 448 **Figure 3.** Comparison of UPS and hot-electron measurements for standard and clean gold. a)  
 449 Ionization potential of the N2200 measured with UPS (Ultraviolet Photoemission  
 450 Spectroscopy). A 90-nm-thick N2200 layer is spin coated on Au (14 nm)/AlOx (20 nm)/SiOx  
 451 (200 nm)/Si. b) Work function of gold measured with UPS. The gold is deposited on top of  
 452 AlOx (20 nm)/SiOx (200 nm)/Si and is covered with 90 nm of N2200. c) Au/N2200 interface  
 453 energy diagram.  $E_F$  is the Fermi energy and  $\Phi_{Au}$  the work function of gold. LUMO  
 454 corresponds to the lowest unoccupied molecular orbital, HOMO to the highest occupied  
 455 molecular orbital, IP to the ionization potential, EA to the electron affinity and  $E_g$  to the  
 456 energy band gap of the N2200 polymer. The integer charge transfer states are represented as  
 457  $E_{ICT+}$  and  $E_{ICT-}$ . d) Measured hot electron current normalized to  $I_{C-hot} / I_{C-hot(max)}$  as a function  
 458 of the applied bias  $V_{EB}$  at 290 K.  $I_{C-hot(max)}$  corresponds to the maximum value of the measured  
 459 hot electron current. The red curve corresponds to the standard device with non-clean base  
 460 gold and the black curve corresponds to oxygen-plasma-cleaned base gold device.

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463 **Figure 4.** Theoretical model for the experimental data. a) Structural model of the  
464 Au/N2200/Al heterostructure. The polymer is represented electronically by hopping sites  
465 (indicated by balls in the central region), which are connected by hopping rates (sticks). b)  
466 Energy levels as a function of distance  $x$  to the Au surface, calculated from the electrostatic  
467 potential (for  $V_{EB}=-1.2$  V). c) Simulated hot-electron current-voltage characteristics (red) and  
468 extrapolation of threshold voltage to -1.2 V (black).

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471 **In this work we demonstrate in-device hot electron spectroscopy as a direct and reliable**  
472 **technique for the determination of the energy barrier between a metal and a solution-**  
473 **processed electron-transporting organic semiconductor.** With our experimental advance, we  
474 open new possibilities to bring this technique closer to the organic electronics industry.

475  
476 **Keywords: Hot electron transistor, spectroscopy, energy barrier, polymer, organic**  
477 **electronics**

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480 Cristian Gozalvez, Roger Llopis, Aurelio Mateo-Alonso, Felix Casanova, Frank Ortman,  
481 Mats Fahlman, Luis E. Hueso\*

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483 **Energy Level Alignment at Metal/Solution-Processed Organic Semiconductor Interfaces**  
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